M59C

Silicon Controlled Switch

Driver for Numerical Indicator Tube Switching

■ Features

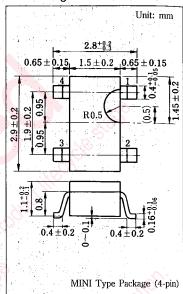
- Selective breakover voltage
- Low On-voltage

■ Absolute Maximum Ratings (Ta=25°C)

	<u> </u>				
Item	Symbol	Value		Unit	
Item		PNP	NPN	Oint	
Collector-Base Voltage	V _{cвo}	-70	70	V	
Collector-Emitter Voltage	V _{CER} *1		70	V	
Collector-Emitter Voltage	V _{CEO}	-70		V	
Emitter-Base Voltage	V _{EBO}	-70	5	V	
Emitter Current	IE	100	-100	mA	
Peak Emitter Current	I _{EM} *2	500	-500	mA.	
Collector Current	Ic) : (V.	50	mA A	
Peak Collector Current	I _{cm}		100	mA	
Power Dissipation	P _D	200		mW	
Junction Temperature	T_1	150		c	
Storage Temperature	T _{stg}	-55~+150		.0°	
*1.70 10.1.0 *24 21	A 0 05				

^{*1} $R_{BE} = 10 \text{ k}\Omega$ *2 tw < 1 ms, $\delta = 0.05$

■ Package Dimensions



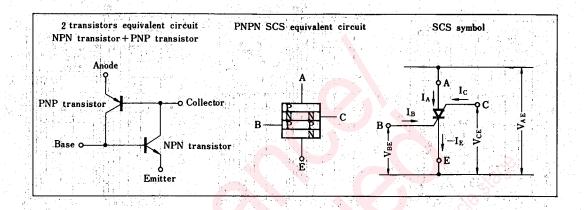
2 :				
	pin	①NPN Part	②PNP Part	③ Integrated Element
	1	Collector	Base	AG
	2		Emitter	A
	3	Emitter		K
×	4	Base	Collector	AG

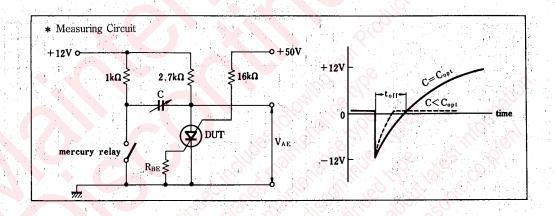
■ Electrical Characteristics (Ta=25°C)

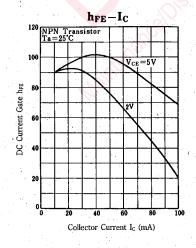
Item	Symbol	Condition	min.	typ.	max.	Unit
(NPN transistor)	<i>D</i> .	0, 0, 0	2/			
Collector Cutoff Current	I _{CER}	$V_{CE} = 70 \text{ V}, R_{BE} = 10 \text{ k}\Omega$		10	100	nA
Emitter Cutoff Current	ІЕВО	$V_{EB} = 5 \text{ V}, I_{C} = 0$		30	1000	nA
DC Current Gain	h _{FE}	$V_{CE}=2 V$, $I_{C}=10 mA$	50	180	-t	
(PNP Transistor)		112 1/4				
Emitter Cutoff Current	I _{EBO}	$V_{EB} = -70 \text{ V}, I_C = 0$		-0.05	-100	• nA
DC Current Gain	h _{FE} *	$V_{CB}=0$, $I_E=1$ mA	0.19	1.1	2.5	
(Coupling Characteristics)			lucc			
Forward Voltage	VAE	$I_A = 50 \text{ mA}, I_C = 0, R_{BE} = 10 \text{ k}\Omega$		1.05	1.4	·v
Holding Current (DC)	I _H	$R_{BE} = 10 \text{ k}\Omega, I_{C} = 10 \text{ mA}, V_{BB} = -2 \text{ V}$	0.1	0.5	1	mA
Turn-off Time	toff	$R_{BE} = 10 \text{ k}\Omega^{*2}$, 11	20	μs

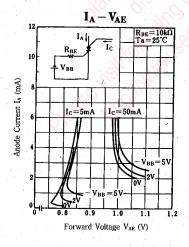
*2tn measuring cirucit

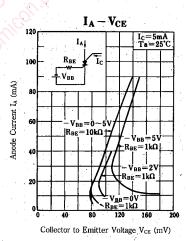
Class	P	Q
$h_{FE}(PNP)$	0.19~1.2	0.72~2.5

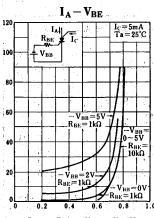


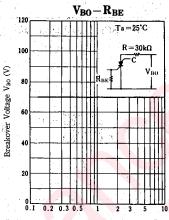


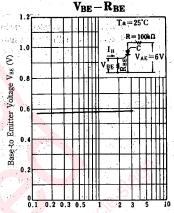








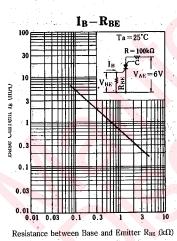


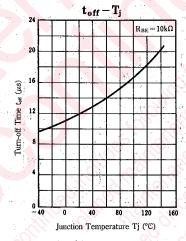


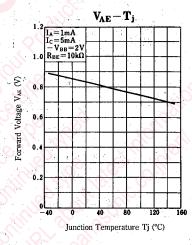
Base to Emitter Voltage V_{BE} (V)

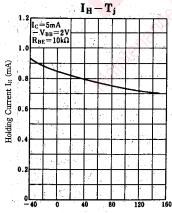
Resistance between Base and Emitter (kΩ)

Resistance between Base and Emitter R_{BE} (kΩ)









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